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45V NPN SMALL SIGNAL TRANSISTOR IN DFN1006

Features

- $BV_{CEO} > 45V$
- I_C = 100mA High Collector Current
- P_D = 1000mW Power Dissipation
- 0.60mm² Package Footprint, 13 times Smaller than SOT23
- 0.4mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type BC857BLP4
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

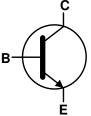
Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0008 grams (Approximate)

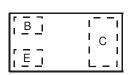
X2-DFN1006-3







Device Symbol



Top View Device Schematic

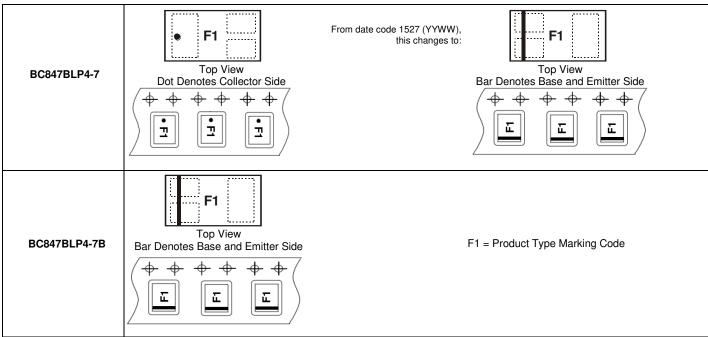
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BC847BLP4-7	F1	7	8mm	3,000
BC847BLP4-7B	F1	7	8mm	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	Ic	100	mA
Peak Pulse Collector Current	I _{CM}	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	400	- mW	
rower Dissipation	(Note 6)	P _D	1000		
Thermal Resistance, Junction to Ambient	(Note 5)	Б	310	°C/M	
mermai nesistance, junction to Ambient	(Note 6)	$R_{ hetaJA}$	120	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ hetaJL}$	120	°C/W	
Operating and Storage and Temperature Rang	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	200	٧	В

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		50	_	_	V	$I_C = 10\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 9)		45	_		٧	$I_C = 10mA, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6	_	_	٧	$I_E = 1\mu A, I_C = 0$
DC Current Gain	h _{FE}	200	350	450	-	$V_{CE} = 5.0V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}		80 200	250 600	mV	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$ $I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	11	700 900		mV	$I_C = 10mA, I_B = 0.5mA$ $I_C = 100mA, I_B = 5.0mA$
Base-Emitter Voltage (Note 9)	V _{BE(on)}	580 —	640 725	700 770	mV	$V_{CE} = 5.0V, I_{C} = 2.0 \text{mA}$ $V_{CE} = 5.0V, I_{C} = 10 \text{mA}$
Collector-Cutoff Current	I _{CBO}			15 5.0	nΑ μΑ	$V_{CB} = 30V$ $V_{CB} = 30V$, $T_{A} = +150$ °C
Gain Bandwidth Product	f _T	100	_	_	MHz	$V_{CE} = 5.0V$, $I_{C} = 10mA$, $f = 100MHz$
Collector-Base Capacitance	C _{CBO}	_	3.0	_	pF	V _{CB} = 10V, f = 1.0MHz

Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper. 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.
- 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

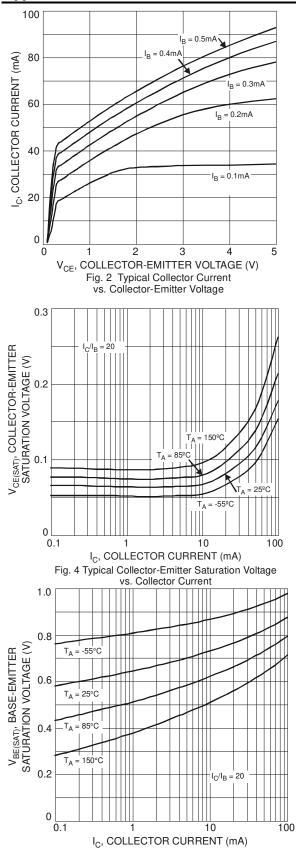


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

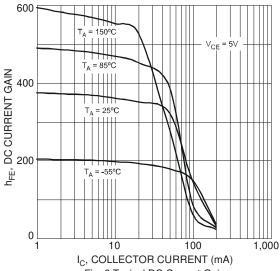


Fig. 3 Typical DC Current Gain
vs. Collector Current

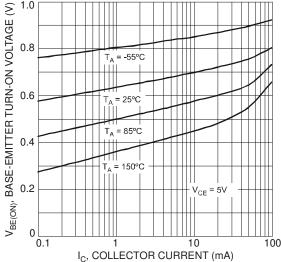
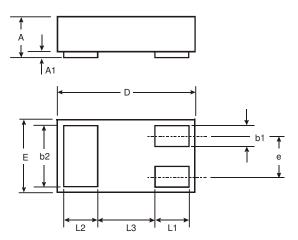


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current



Package Outline Dimensions

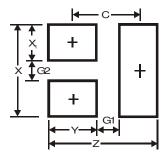
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1006-3					
Dim	Min	Max	Тур		
Α	_	0.40			
A1	0	0.05	0.02		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	_	_	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	_	_	0.40		
All	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	1.1		
G1	0.3		
G2	0.2		
Х	0.7		
X1	0.25		
Υ	0.4		
С	0.7		



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